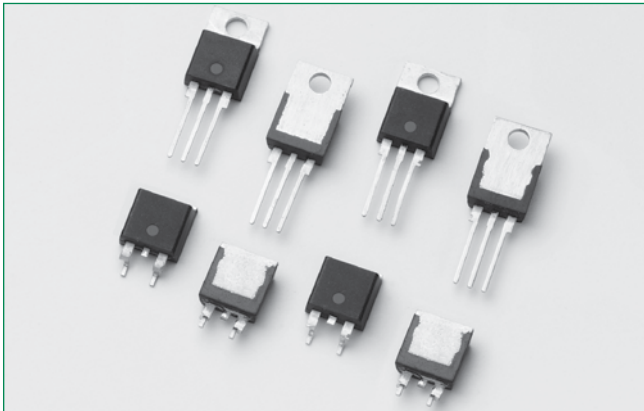


Qxx12xHx Series



**Agency Approval**

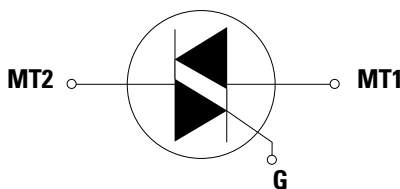
Agency	Agency File Number
	E71639*

\* - L Package Only

**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM}/V_{RRM}$	400, 600, 800 or 1000	V
$I_{GT(Q1)}$	10 or 50	mA

**Schematic Symbol**



**Description**

This 12 Amp bidirectional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard alternistor triac components operate with in-phase signals in Quadrants I or III and ONLY unipolar negative gate pulses for Quadrant II or III. The alternistor triac will not operate in Quadrant IV. These are used in circuit applications requiring a high dv/dt capability.

**Features & Benefits**

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 120 A
- The L-package has an isolation rating of 2500V<sub>RMS</sub>
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point sine wave
- Requires only a small gate activation pulse in each half-cycle
- Recognized to UL 1557 as an Electrically Isolated Semiconductor Device

**Applications**

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

**Additional Information**



Datasheet



Resources



Samples

### Absolute Maximum Ratings — Alternistor (3 Quadrants)

Symbol	Parameter	Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx12LHy $T_c = 90^\circ\text{C}$	12	A
		Qxx12RHHy Qxx12NHHy $T_c = 105^\circ\text{C}$		
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_j$ initial = $25^\circ\text{C}$ )	f = 50 Hz t = 20 ms	110	A
		f = 60 Hz t = 16.7 ms	120	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms	60	$\text{A}^2\text{s}$
di/dt	Critical rate of rise of on-state current	f = 120 Hz $T_j = 125^\circ\text{C}$	70	$\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate trigger current	$t_p = 20$ $\mu\text{s}$ $T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.5	W
$T_{stg}$	Storage temperature range		-40 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

Note: xx = voltage/10, y = sensitivity

### Electrical Characteristics ( $T_j = 25^\circ\text{C}$ , unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant	Qxx12xH2	Qxx12xH5	Unit	
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III	MAX.	10	50	mA
$V_{GT}$	$V_D = 12\text{V}$ $R_L = 60\ \Omega$	I – II – III	MAX.	1.3	1.3	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_j = 125^\circ\text{C}$	I – II – III	MIN.	0.2	0.2	V
$I_H$	$I_T = 100\text{mA}$		MAX.	15	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_j = 125^\circ\text{C}$	400V	MIN.	300	750	V/ $\mu\text{s}$
		600V		200	650	
		800V		150	500	
	$V_D = V_{DRM}$ Gate Open $T_j = 100^\circ\text{C}$	1000V	150	300		
(dv/dt)c	(di/dt)c = 6.5 A/ms $T_j = 125^\circ\text{C}$		MIN.	2	30	V/ $\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 17.0\ \text{A(pk)}$		TYP.	4	4	$\mu\text{s}$

### Static Characteristics

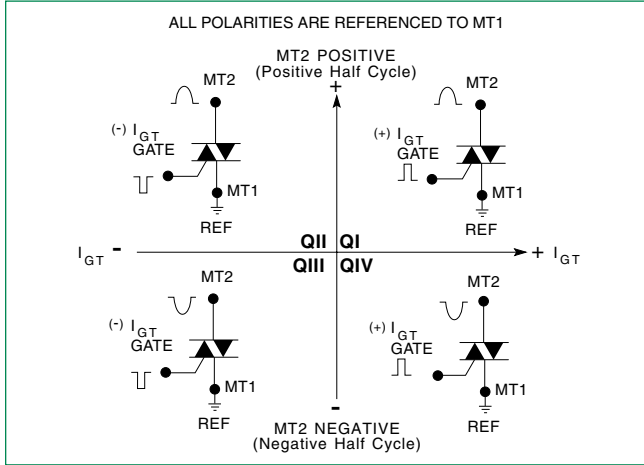
Symbol	Test Conditions	Value	Unit		
$V_{TM}$	$I_{TM} = 17.0\text{A}$ $t_p = 380\ \mu\text{s}$	MAX.	1.60	V	
$I_{DRM}$ $I_{RRM}$	$V_D = V_{DRM} / V_{RRM}$	$T_j = 25^\circ\text{C}$ 400-1000V	MAX.	10	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$ 400-800V		2	mA
		$T_j = 100^\circ\text{C}$ 1000V		3	

### Thermal Resistances

Symbol	Parameter	Value	Unit	
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx12RHHy Qxx12NHHy	1.2	$^\circ\text{C}/\text{W}$
		Qxx12LHy	2.3	
$R_{\theta(J-A)}$	Junction to ambient (AC)	Qxx12RHHy	45	$^\circ\text{C}/\text{W}$
		Qxx12LHy	90	

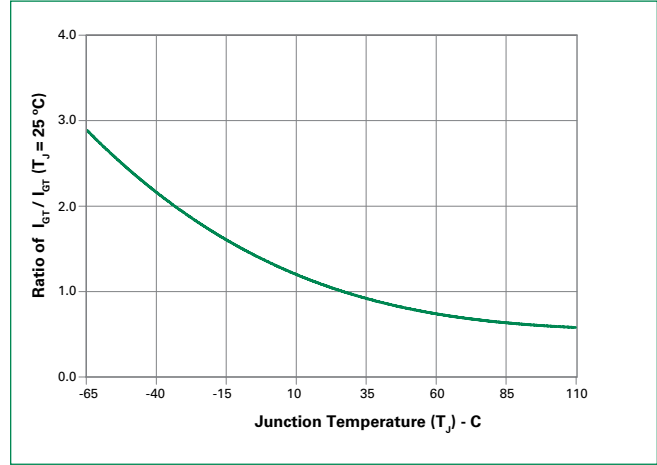
Note: xx = voltage/10, y = sensitivity

**Figure 1: Definition of Quadrants**

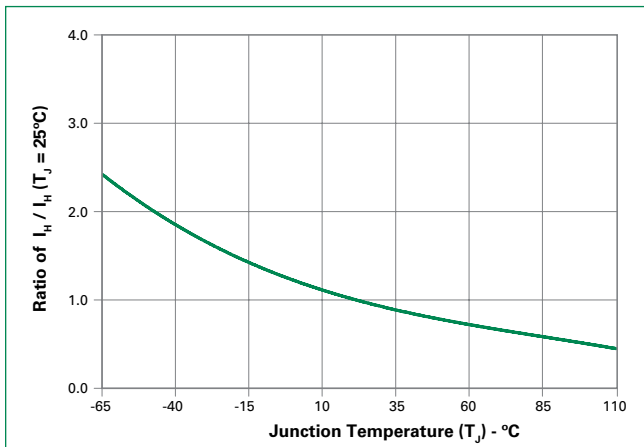


Note: Alternistors will not operate in QIV

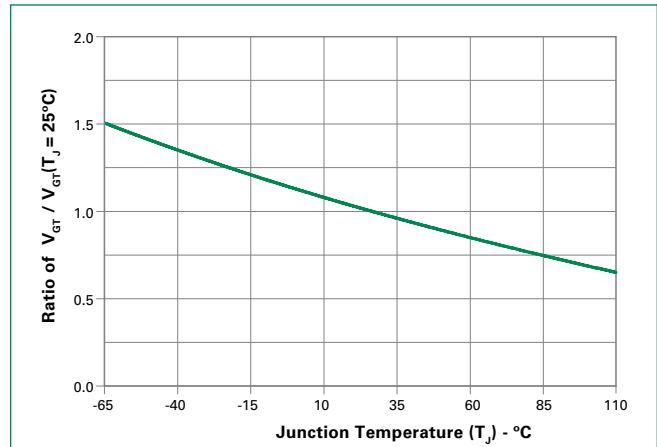
**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**



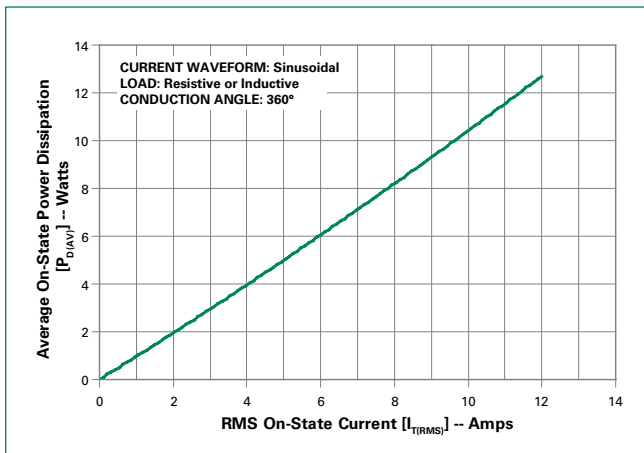
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



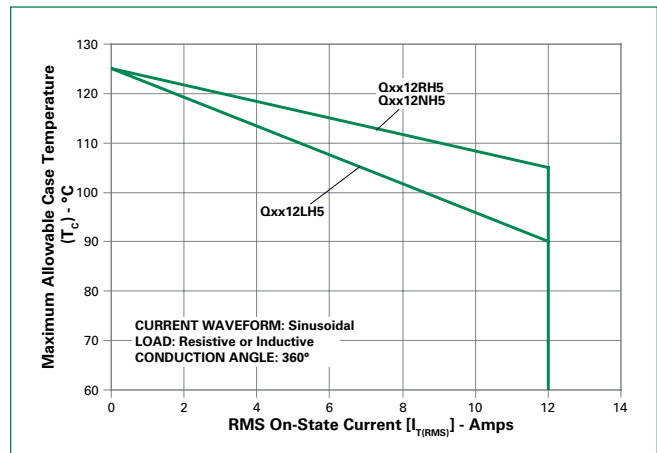
**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**



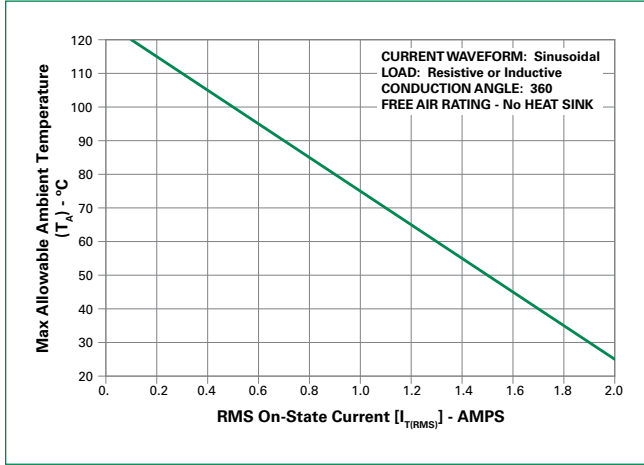
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



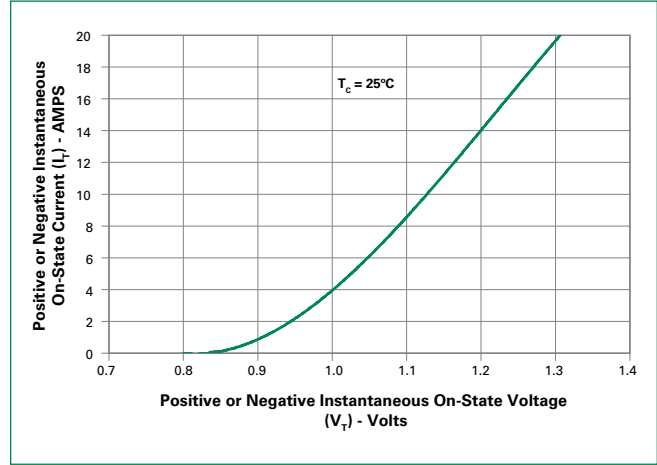
**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**



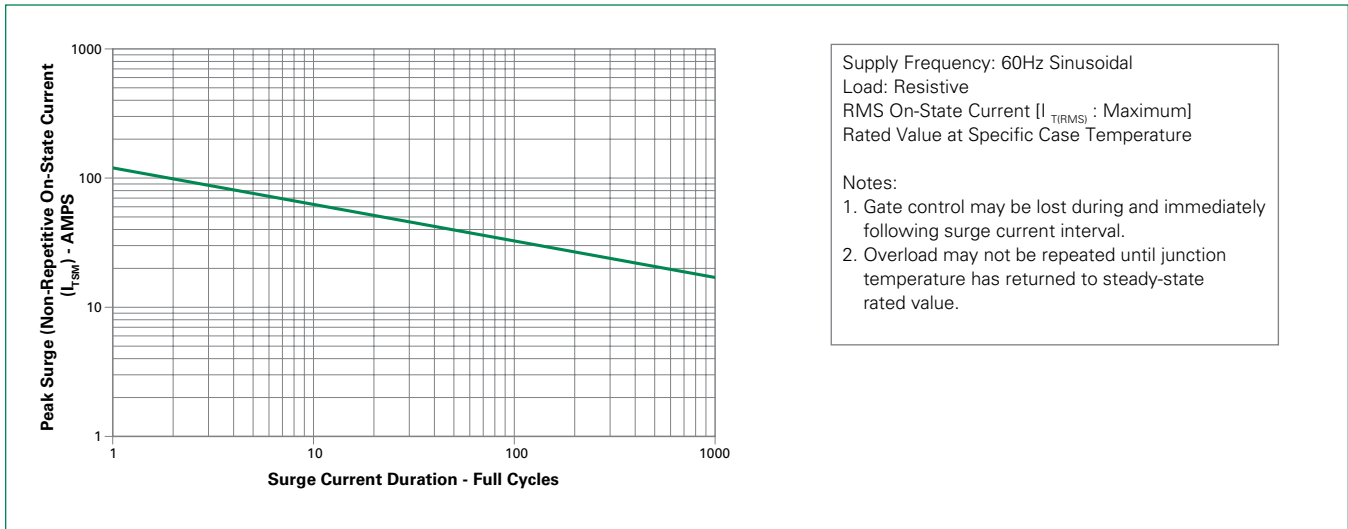
**Figure 7: Maximum Allowable Ambient Temperature vs. On-State Current**



**Figure 8: On-State Current vs. On-State Voltage (Typical)**

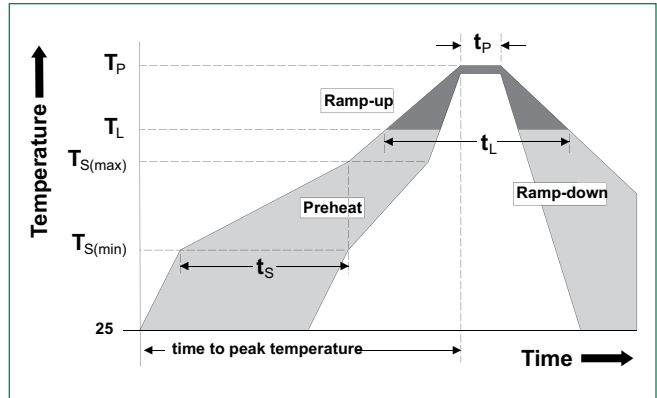


**Figure 9: Surge Peak On-State Current vs. Number of Cycles**



**Soldering Parameters**

<b>Reflow Condition</b>		Pb – Free assembly
<b>Pre Heat</b>	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
<b>Average ramp up rate (Liquidus Temp) (<math>T_L</math>) to peak</b>		5°C/second max
<b><math>T_{s(max)}</math> to <math>T_L</math> - Ramp-up Rate</b>		5°C/second max
<b>Reflow</b>	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time (min to max) ( $t_s$ )	60 – 150 seconds
<b>Peak Temperature (<math>T_p</math>)</b>		260 <sup>+0/-5</sup> °C
<b>Time within 5°C of actual peak Temperature (<math>t_p</math>)</b>		20 – 40 seconds
<b>Ramp-down Rate</b>		5°C/second max
<b>Time 25°C to peak Temperature (<math>T_p</math>)</b>		8 minutes Max.
<b>Do not exceed</b>		280°C



**Physical Specifications**

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL Recognized compound meeting flammability rating V-0
<b>Terminal Material</b>	Copper Alloy

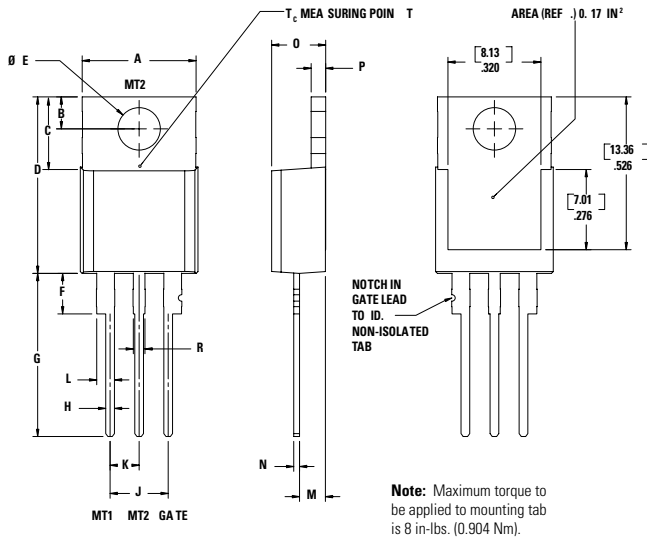
**Design Considerations**

Careful selection of the correct component for the application’s operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

**Environmental Specifications**

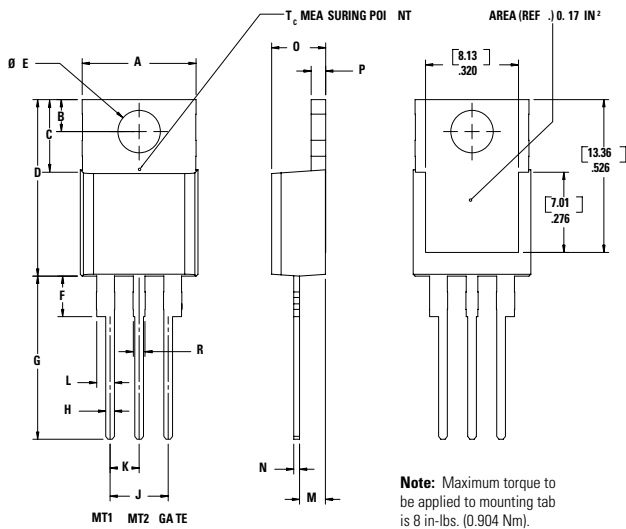
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

### Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



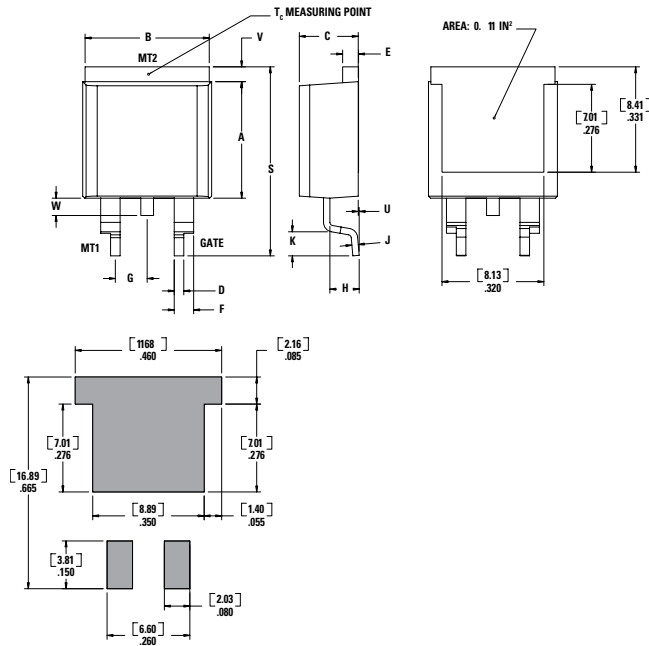
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-263AB (N-Package) — D<sup>2</sup>Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

### Product Selector

Part Number	Voltage				Gate Sensitivity Quadrants I – II – III	Type	Package
	400V	600V	800V	1000V			
Qxx12LH2	X	X	X		10 mA	Alternistor Triac	TO-220L
Qxx12RH2	X	X	X		10 mA	Alternistor Triac	TO-220R
Qxx12NH2	X	X	X		10 mA	Alternistor Triac	TO-263 D <sup>2</sup> PAK
Qxx12LH5	X	X	X	X	50 mA	Alternistor Triac	TO-220L
Qxx12RH5	X	X	X	X	50 mA	Alternistor Triac	TO-220R
Qxx12NH5	X	X	X	X	50 mA	Alternistor Triac	TO-263 D <sup>2</sup> PAK

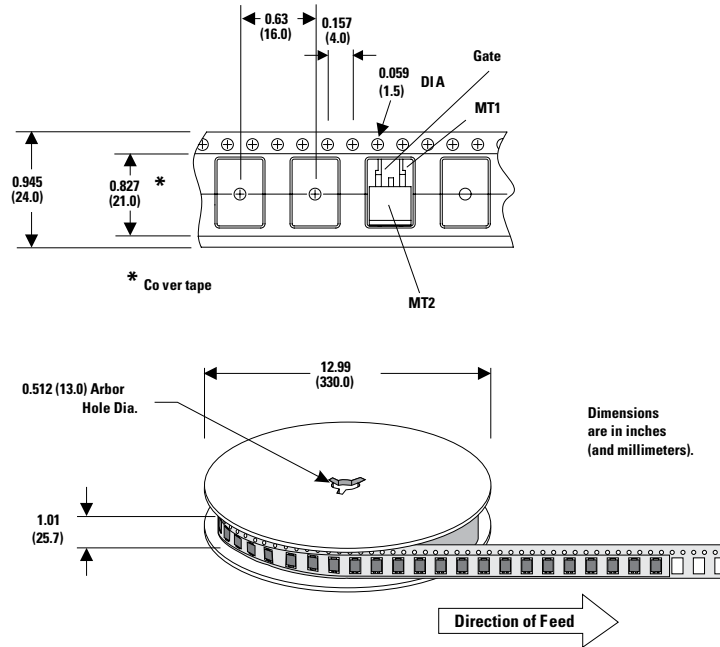
### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx12L/RHyTP	Qxx12L/RHy	2.2 g	Tube Pack	500 (50 per tube)
Qxx12NHyTP	Qxx12NHy	1.6 g	Tube	500 (50 per tube)
Qxx12NHyRP	Qxx12NHy	1.6 g	Embossed Carrier	500

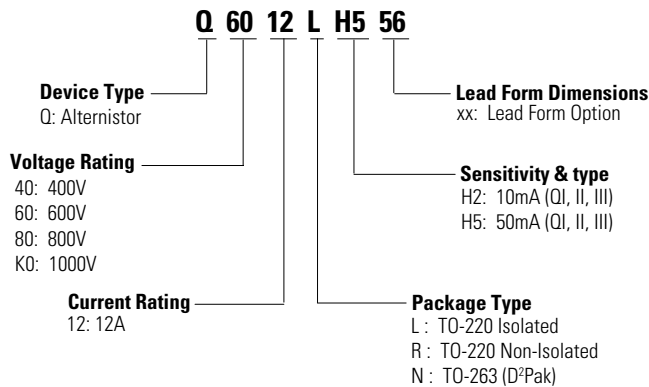
Note: xx = Voltage/10; y = Sensitivity

### TO-263 Embossed Carrier Reel Pack (RP)

Meets all EIA-481-2 Standards

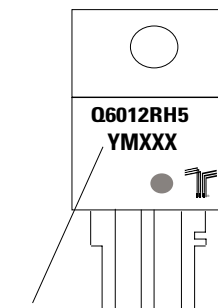


### Part Numbering System



### Part Marking System

TO-220 AB - (L and R Package)  
TO-263 AB - (N Package)



Date Code Marking  
Y: Year Code  
M: Month Code  
XXX: Lot Trace Code